COS/MOS BCD Rate Multiplier

High-Voltage Types (20-Volt Rating)

The RCA-CD4527B is a low-power 4-bit digital rate multiplier that provides an output-pulse rate which is the clock-input-pulse rate multiplied by 1/10 times the BCD input. For example, when the BCD input is 8, there will be 8 output pulses for every 10 input pulses. This device may be used to perform arithmetic operations (add, subtract, divide, raise to a power), solve algebraic and differential equations, generate natural logarithms and trigonometric functions, A/D and D/A conversion, and frequency division.

For fractional multipliers with more than one digit, CD4527B devices may be cascaded in two different modes: the Add mode and the Multiply mode. (See Figs.12 and 15). In the Add mode,

$$\text{Output Rate} = (\text{Clock Rate})\left[0.1\ BCD_1 + 0.01\ BCD_2 + 0.001\ BCD_3 + \cdots\right]$$

In the Multiply mode, the fraction programmed into the first rate multiplier is multiplied by the fraction programmed into the second one,

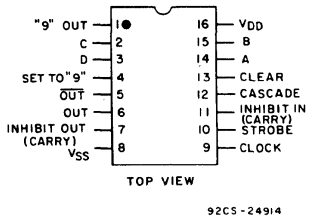
$$\text{e.g.}\ \frac{9}{10} \times \frac{4}{10} = \frac{36}{100}\ \text{or 36 output}$$

pulses for every 100 clock input pulses.

The CD4527B types are supplied in 16-lead ceramic dual-in-line packages (D and F suffixes), 16-lead dual-in-line plastic packages (E suffix), 16-lead ceramic flat packages (K suffix), and in chip form (H suffix).

Applications:

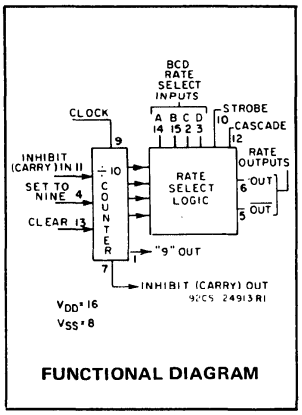
- **Numerical control**
- **Instrumentation**
- **Digital filtering**
- **Frequency synthesis**



TERMINAL ASSIGNMENT

Features:

- **Cascadable in multiples of 4-bits**
- **Set to "9" input and "9" detect output**
- **100% test for quiescent current at 20 V**
- **5-V, 10-V, and 15-V parametric ratings**
- **Standardized, symmetrical output characteristics**
- **Maximum input current of 1 μA at 18 V over full package-temperature range; 100 nA at 18 V and 25°C**
- **Noise margin (full package-temperature range) =**
  - **1 V at V_{DD} = 5 V**
  - **2 V at V_{DD} = 10 V**
  - **2.5 V at V_{DD} = 15 V**
- **Meets all requirements of JEDEC Tentative Standard No.13A, "Standard Specifications for Description of 'B' Series CMOS Devices"**



FUNCTIONAL DIAGRAM

MAXIMUM RATINGS, *Absolute-Maximum Values:*

DC SUPPLY-VOLTAGE RANGE, (V_{DD})
(Voltages referenced to V_{SS} Terminal) . . . . . −0.5 to +20 V
INPUT VOLTAGE RANGE, ALL INPUTS . . . . . −0.5 to V_{DD} +0.5 V
DC INPUT CURRENT, ANY ONE INPUT . . . . . ±10 mA
POWER DISSIPATION PER PACKAGE (P_D):
For T_A = −40 to +60°C (PACKAGE TYPE E) . . . . . 500 mW
For T_A = +60 to +85°C (PACKAGE TYPE E) . . . . . Derate Linearly at 12 mW/°C to 200 mW
For T_A = −55 to +100°C (PACKAGE TYPES D, F) . . . . . 500 mW
For T_A = +100 to +125°C (PACKAGE TYPES D, F) . . Derate Linearly at 12 mW/°C to 200 mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR
FOR T_A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types) . . . . . 100 mW
OPERATING-TEMPERATURE RANGE (T_A):
PACKAGE TYPES D, F, H . . . . . −55 to +125°C
PACKAGE TYPE E . . . . . −40 to +85°C
STORAGE TEMPERATURE RANGE (T_{stg}) . . . . . −65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 ± 1/32 inch (1.59 ± 0.79 mm) from case for 10 s max. . . . . +265°C

RECOMMENDED OPERATING CONDITIONS AT T_A = 25°C, Except as Noted.
For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	V_{DD} (V)	LIMITS Min.	LIMITS Max.	UNITS
Supply-Voltage Range (For T_A = Full Package-Temperature Range)		3	18	V
Set or Clear Pulse Width, t_W	5	160	–	ns
	10	90	–	
	15	60	–	
Clock Pulse Width, t_W	5	330	–	ns
	10	170	–	
	15	100	–	
Clock Frequency, f_{CL}	5	dc	1.2	MHz
	10		2.5	
	15		3.5	
Clock Rise or Fall Time, t_{rCL} or t_{fCL}	5,10,15	–	15	μs
Inhibit In Setup Time, t_{SU}	5	100	–	ns
	10	40	–	
	15	20	–	
Inhibit In Removal Time, t_{REM}	5	240	–	ns
	10	130	–	
	15	110	–	
Set Removal Time, t_{REM}	5	150	–	ns
	10	80	–	
	15	50	–	
Clear Removal Time, t_{REM}	5	60	–	ns
	10	40	–	
	15	30	–	

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C) Values at −55, +25, +125 Apply to D, F, H Packages Values at −40, +25, +85 Apply to E Package							UNITS
									+25		
	V_O (V)	V_{IN} (V)	V_{DD} (V)	−55	−40	+85	+125	Min.	Typ.	Max.	
Quiescent Device Current, I_{DD} Max.	–	0,5	5	5	5	150	150	–	0.04	5	μA
	–	0,10	10	10	10	300	300	–	0.04	10	
	–	0,15	15	20	20	600	600	–	0.04	20	
	–	0,20	20	100	100	3000	3000	–	0.08	100	
Output Low (Sink) Current I_{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	–	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	–	
	1.5	0,15	15	4.2	4	2.8	2.4	3 4	6.8	–	
Output High (Source) Current, I_{OH} Min.	4.6	0,5	5	−0.64	−0.61	−0.42	−0.36	−0.51	−1	–	
	2.5	0,5	5	−2	−1.8	−1.3	−1.15	−1.6	−3.2	–	
	9.5	0,10	10	−1.6	−1.5	−1.1	−0.9	−1.3	−2.6	–	
	13.5	0,15	15	−4.2	−4	−2.8	−2.4	−3.4	−6.8	–	
Output Voltage: Low-Level, V_{OL} Max.	–	0,5	5	0.05				–	0	0.05	V
	–	0,10	10	0.05				–	0	0.05	
	–	0,15	15	0.05				–	0	0.05	
Output Voltage: High-Level, V_{OH} Min.	–	0,5	5	4.95				4.95	5	–	
	–	0,10	10	9.95				9.95	10	–	
	–	0,15	15	14.95				14.95	15	–	
Input Low Voltage, V_{IL} Max.	0.5, 4.5	–	5	1.5				—	—	1.5	V
	1, 9	–	10	3				—	—	3	
	1.5, 13.5	–	15	4				—	—	4	
Input High Voltage, V_{IH} Min.	0.5, 4.5	–	5	3.5				3.5	—	—	
	1, 9	–	10	7				7	—	—	
	1.5, 13.5	–	15	11				11	—	—	
Input Current I_{IN} Max.		0,18	18	±0.1	±0.1	±1	±1	–	$\pm 10^{-5}$	±0.1	μA

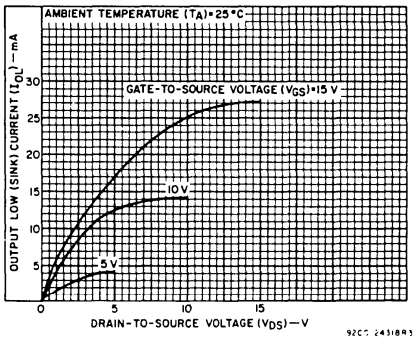


Fig.1 – Typical output low (sink) current characteristics.

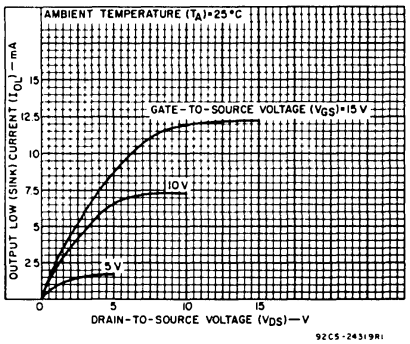


Fig.2 – Minimum output low (sink) current characteristics.

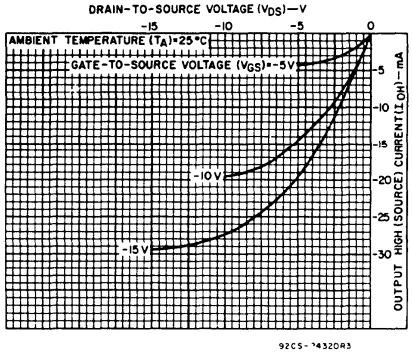


Fig.3 – Typical output high (source) current characteristics.

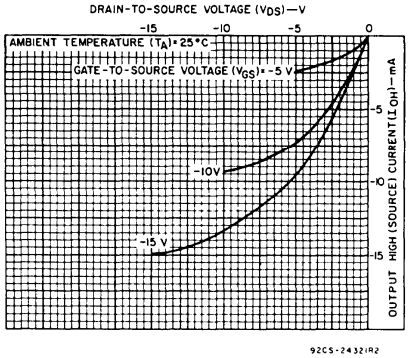


Fig.4 – Minimum output high (source) current characteristics.

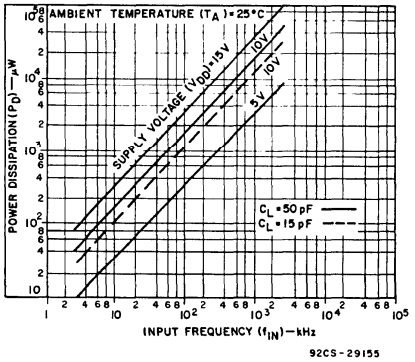


Fig.5 – Typical dynamic power dissipation as a function of input frequency.

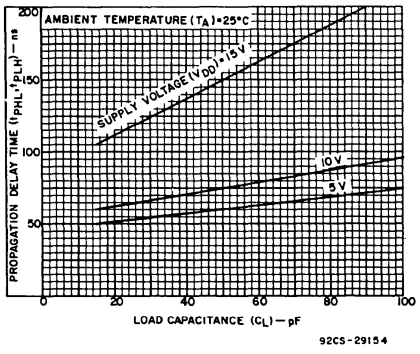


Fig.6 – Typical propagation delay time as a function of load capacitance (Clock or Strobe to Out).

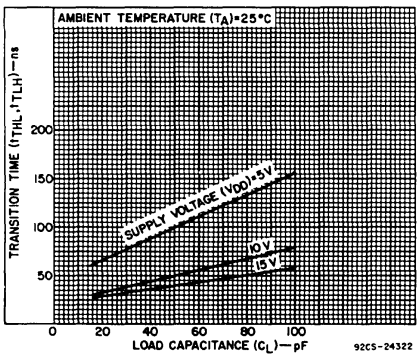


Fig.7 – Typical transition time as a function of load capacitance.

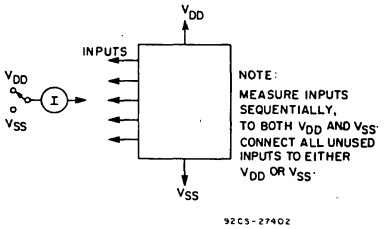


Fig.8 – Input current test circuit.

CD4527B Types

DYNAMIC ELECTRICAL CHARACTERISTICS at T_A = 25°C:
Input t_r,t_f = 20 ns, C_L = 50 pF, R_L = 200 kΩ

CHARACTERISTIC	TEST CONDITIONS	V_{DD} (V)	LIMITS Min.	Typ.	Max.	UNITS
Propagation Delay Time, t_{PHL}, t_{PLH} Clock to $\overline{Out}$		5	–	110	220	ns
		10	–	55	110	
		15	–	45	90	
Clock or Strobe to Out		5	–	150	300	
		10	–	75	150	
		15	–	60	120	
Clock to Inhibit Out High Level to Low Level		5	–	320	640	ns
		10	–	145	290	
		15	–	100	200	
Low Level to High Level		5	–	250	500	
		10	–	100	200	
		15	–	75	150	
Clear to Out		5	–	380	760	ns
		10	–	175	350	
		15	–	130	260	
Clock to "9" or "15" Out		5	–	300	600	
		10	–	125	250	
		15	–	90	180	
Cascade to Out		5	–	90	180	ns
		10	–	45	90	
		15	–	35	70	
Inhibit In to Inhibit Out		5	–	130	260	
		10	–	60	120	
		15	–	45	90	
Set to Out		5	–	330	660	ns
		10	–	150	300	
		15	–	110	220	
Transition Time, t_{THL}, t_{TLH}		5	–	100	200	
		10	–	50	100	
		15	–	40	80	
Maximum Clock Frequency, f_{CL}		5	1.2	2.4	–	MHz
		10	2.5	5	–	
		15	3.5	7	–	
Minimum Clock Pulse Width, t_W		5	–	165	330	ns
		10	–	85	170	
		15	–	50	100	
Clock Rise or Fall Time, t_{rCL}, t_{fCL}		5	–	–	15	μs
		10	–	–	15	
		15	–	–	15	
Minimum Set or Clear Pulse Width, t_W		5	–	80	160	ns
		10	–	45	90	
		15	–	30	60	
Minimum Inhibit In Setup Time, t_{SU}		5	–	50	100	
		10	–	20	40	
		15	–	10	20	
Minimum Inhibit In Removal Time, t_{REM}		5	–	120	240	ns
		10	–	65	130	
		15	–	55	110	
Minimum Set Removal Time, t_{REM}		5	–	75	150	
		10	–	40	80	
		15	–	25	50	
Minimum Clear Removal Time, T_{REM}		5	–	30	60	ns
		10	–	20	40	
		15	–	15	30	
Input Capacitance, C_{IN}	Any Input		–	5	7.5	pF

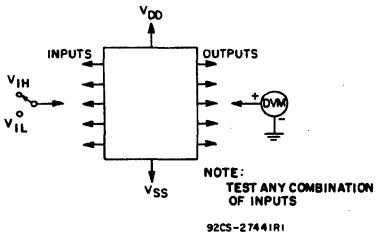


Fig.9 – Input voltage test circuit.

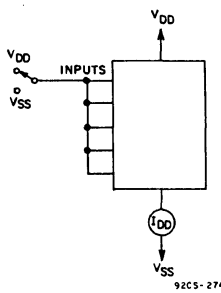


Fig.10 – Quiescent device current test circuit.

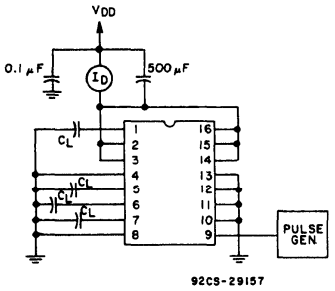


Fig.11 – Dynamic power dissipation test circuit.

APPLICATIONS

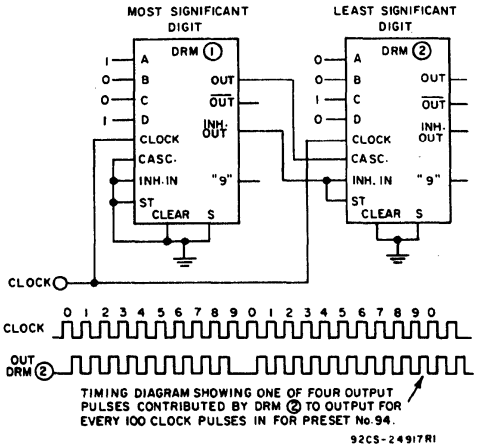


Fig.12 – Two CD4527B's cascaded in the "Add" mode with a preset number of 94 $\left(\frac{9}{10}+\frac{4}{100}=\frac{94}{100}\right)$.

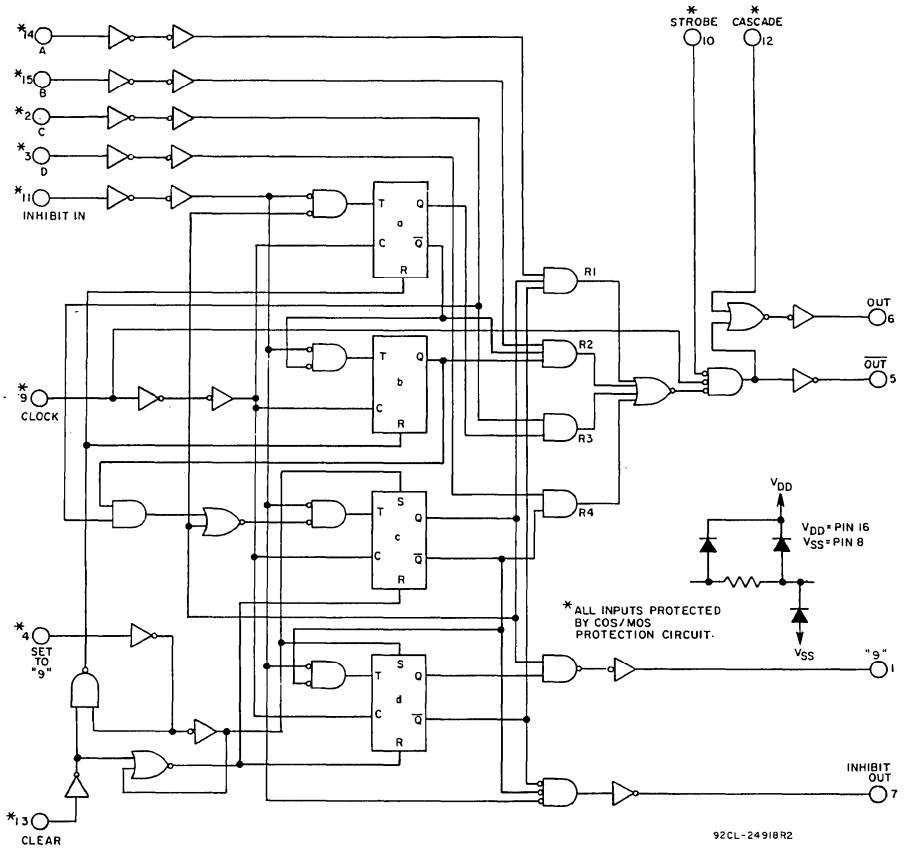


Fig. 13 – Logic diagram.

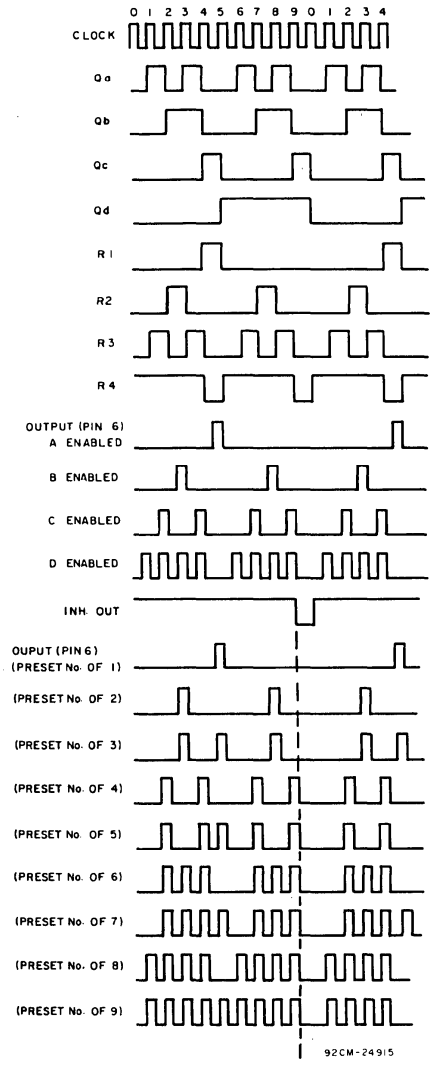
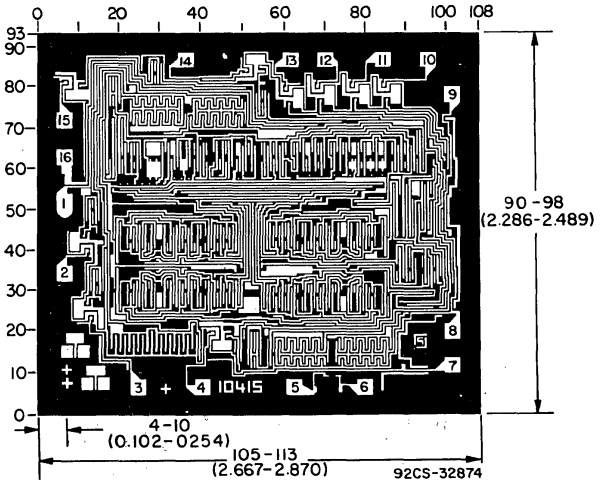


Fig. 14 – Timing diagram (See Logic Diagram).



Dimensions and Pad Layout for CD4527BH

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

The photographs and dimensions of each COS/MOS chip represent a chip when it is part of the wafer. When the wafer is cut into chips, the cleavage angles are 57° instead of 90° with respect to the face of the chip. Therefore, the isolated chip is actually 7 mils (0.17 mm) larger in both dimensions.

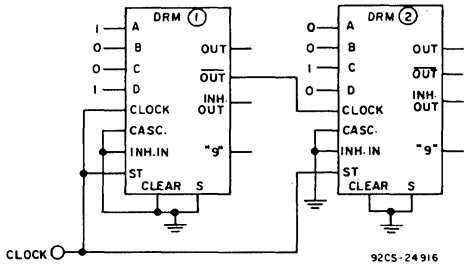


Fig. 15 – Two CD4527B's cascaded in the "Multiply" mode with a preset number of 36 $\left(\frac{9}{10} \times \frac{4}{10} = \frac{36}{100}\right)$.

TRUTH TABLE

INPUTS										OUTPUTS			
Number of Pulses or Input Logic Level (0 = Low; 1 = High; X = Don't Care)										Number of Pulses or Output Logic Level (L = Low; H = High)			
D	C	B	A	CLK	INH IN	STR	CAS	CLR #	SET #	OUT	$\overline{OUT}$	INH OUT	"9" OUT
0	0	0	0	10	0	0	0	0	0	L	H	1	1
0	0	0	1	10	0	0	0	0	0	1	1	1	1
0	0	1	0	10	0	0	0	0	0	2	2	1	1
0	0	1	1	10	0	0	0	0	0	3	3	1	1
0	1	0	0	10	0	0	0	0	0	4	4	1	1
0	1	0	1	10	0	0	0	0	0	5	5	1	1
0	1	1	0	10	0	0	0	0	0	6	6	1	1
0	1	1	1	10	0	0	0	0	0	7	7	1	1
1	0	0	0	10	0	0	0	0	0	8	8	1	1
1	0	0	1	10	0	0	0	0	0	9	9	1	1
1	0	1	0	10	0	0	0	0	0	8	8	1	1
1	0	1	1	10	0	0	0	0	0	9	9	1	1
1	1	0	0	10	0	0	0	0	0	8	8	1	1
1	1	0	1	10	0	0	0	0	0	9	9	1	1
1	1	1	0	10	0	0	0	0	0	8	8	1	1
1	1	1	1	10	0	0	0	0	0	9	9	1	1
X	X	X	X	10	1	0	0	0	0	†	†	H	†
X	X	X	X	10	0	1	0	0	0	L	H	1	1
X	X	X	X	10	0	0	1	0	0	H	*	1	1
1	X	X	X	10	0	0	0	1	0	10	10	H	L
0	X	X	X	10	0	0	0	1	0	L	H	H	L
X	X	X	X	10	0	0	0	0	1	L	H	L	H

* Output same as the first 16 lines of this truth table (depending on values of A, B, C, D).

†Depends on internal state of counter.

#Clear and Set Inputs should not be high at the same time; device draws increased quiescent current when in this non-valid state.